

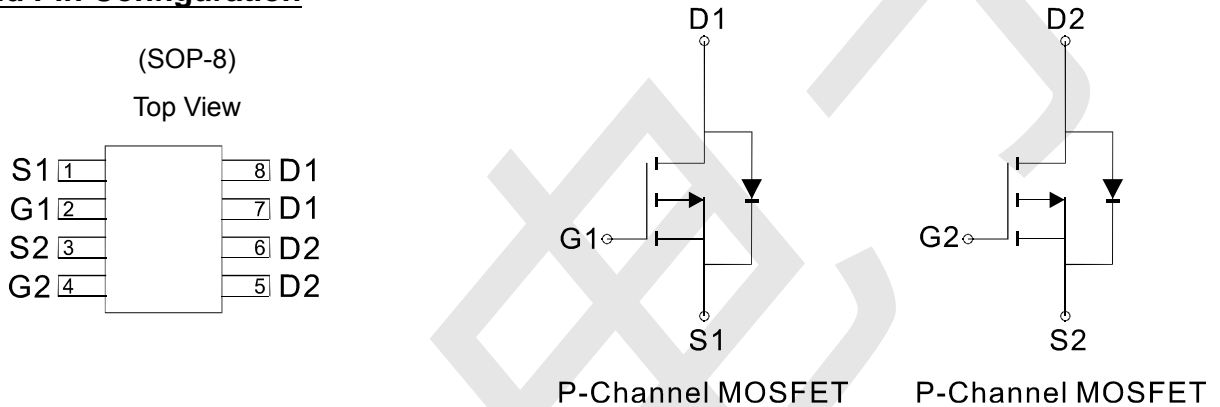
### FEATURES

- $R_{DS(ON)} = 60\text{m}\Omega @ V_{GS} = -10\text{V (Max)}$
- $R_{DS(ON)} = 90\text{m}\Omega @ V_{GS} = -4.5\text{V (Max)}$

### APPLICATIONS

- Power Management in Note book
- Portable Equipment
- Battery Powered System
- DC/DC Converter
- Load Switch
- DSC
- LCD Display inverter

### Package and Pin Configuration



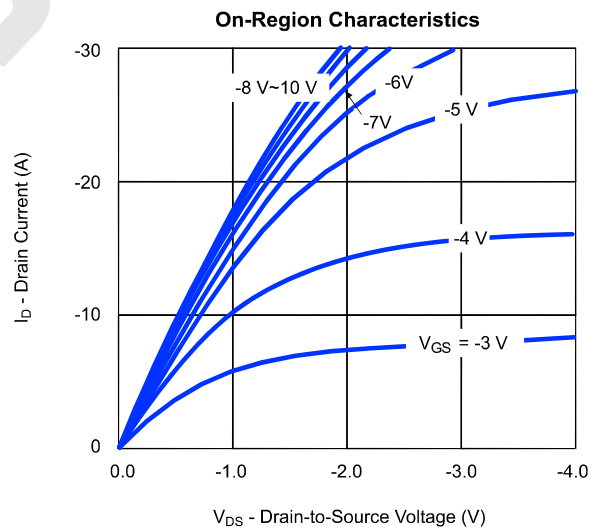
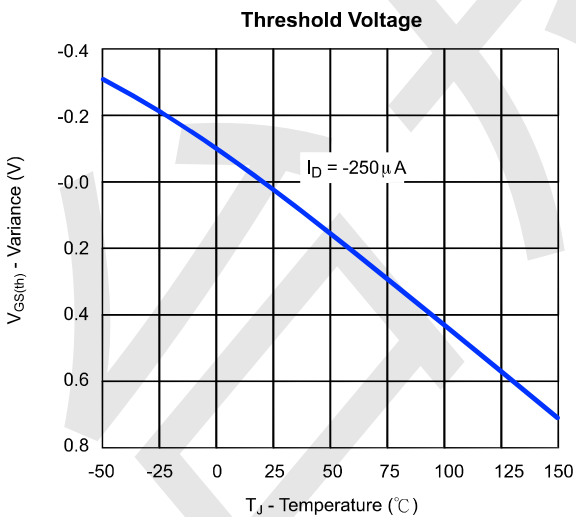
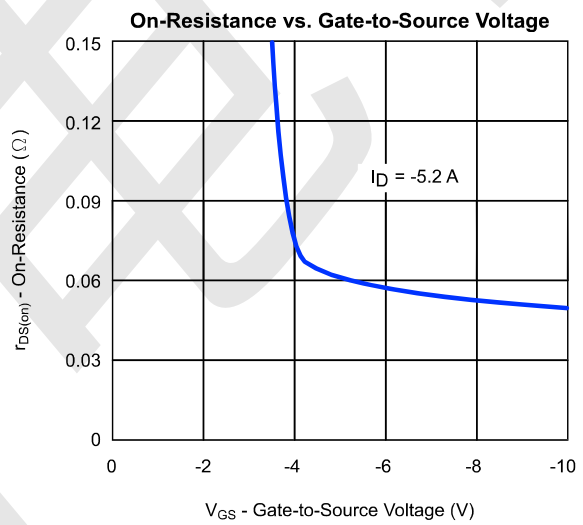
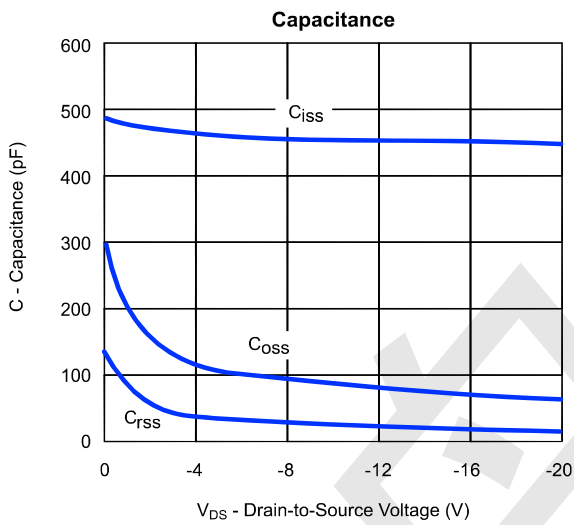
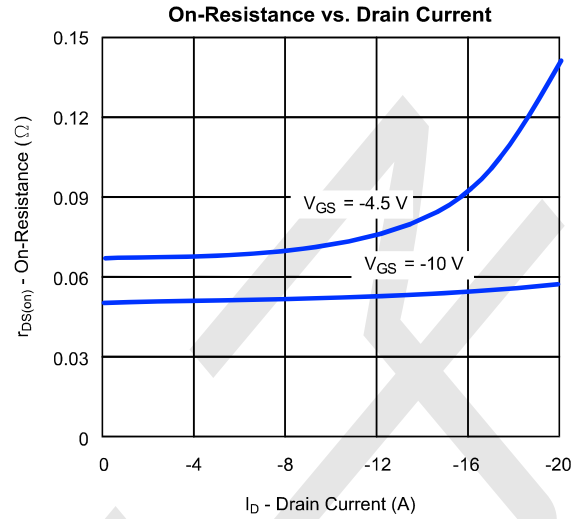
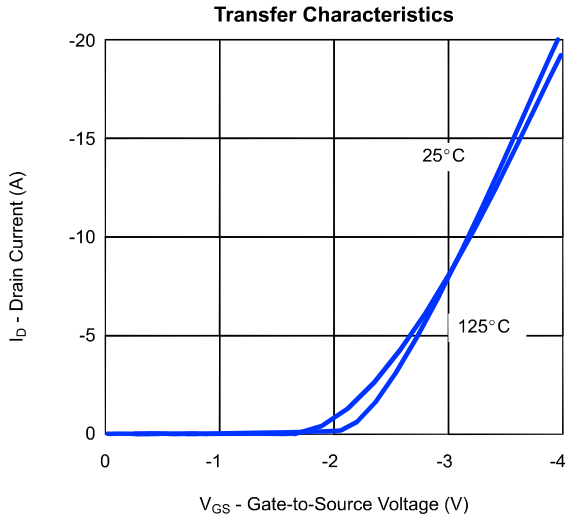
### Absolute Maximum Ratings ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

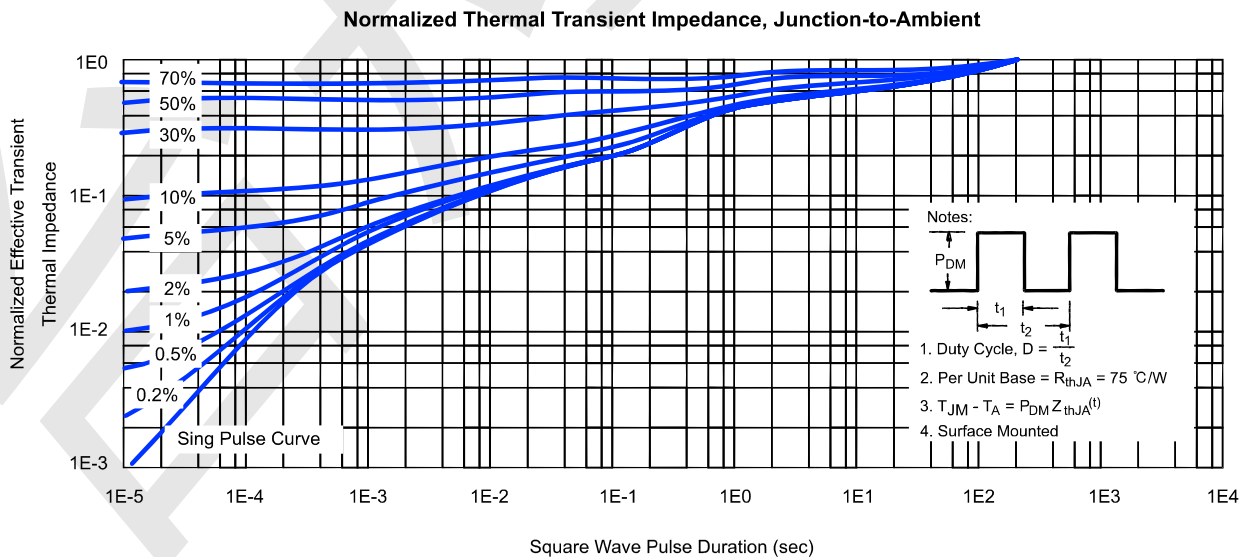
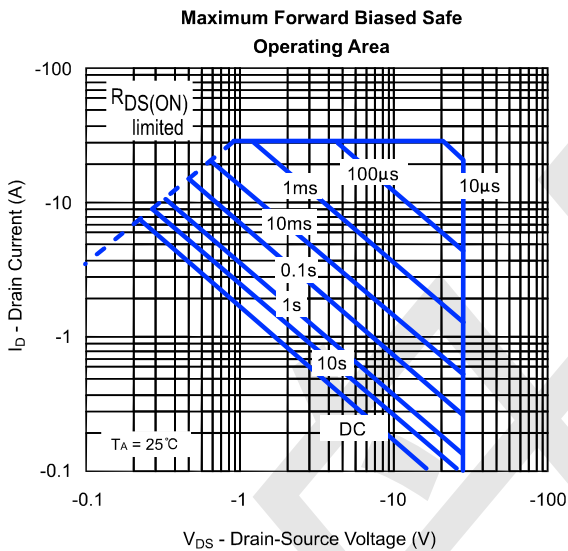
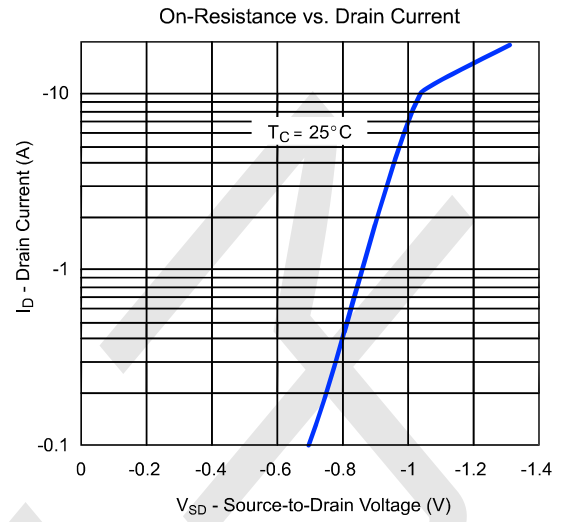
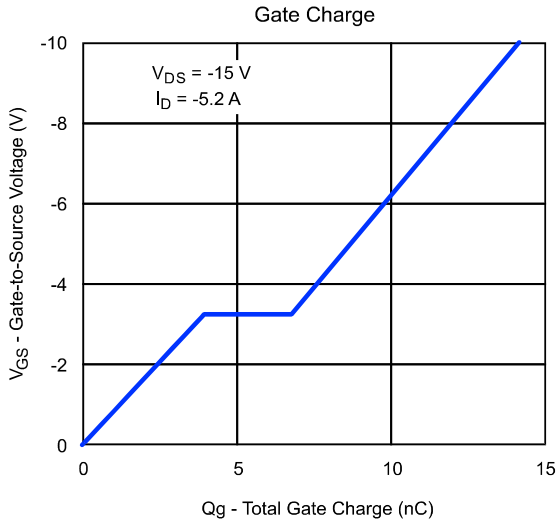
Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	$V_{DSS}$	-30	V	
Gate-Source Voltage	$V_{GSS}$	$\pm 20$	V	
Continuous Drain Current ( $T_j = 150^\circ\text{C}$ )	$I_D$	$T_A = 25$	-5.3	A
		$T_A = 70$	-4.3	
Pulsed Drain Current	$I_{DM}$	-30	A	
Continuous Source Current (Diode Conduction)	$I_S$	-1.7	A	
Maximum Power Dissipation	$P_D$	$T_A = 25$	2.0	W
		$T_A = 70$	1.3	
Operating Junction Temperature	$T_J$	-55 to 150		
Storage Temperature Range	$T_{stg}$	-55 to 150		
Thermal Resistance-Junction to Ambient*	$R_{\theta JA}$	T 10 sec	47	W
		Steady State	75	
Thermal Resistance-Junction to Case	$R_{\theta JC}$	45	W	

**Electrical Characteristics (T<sub>j</sub>=25°C unless otherwise noted)**

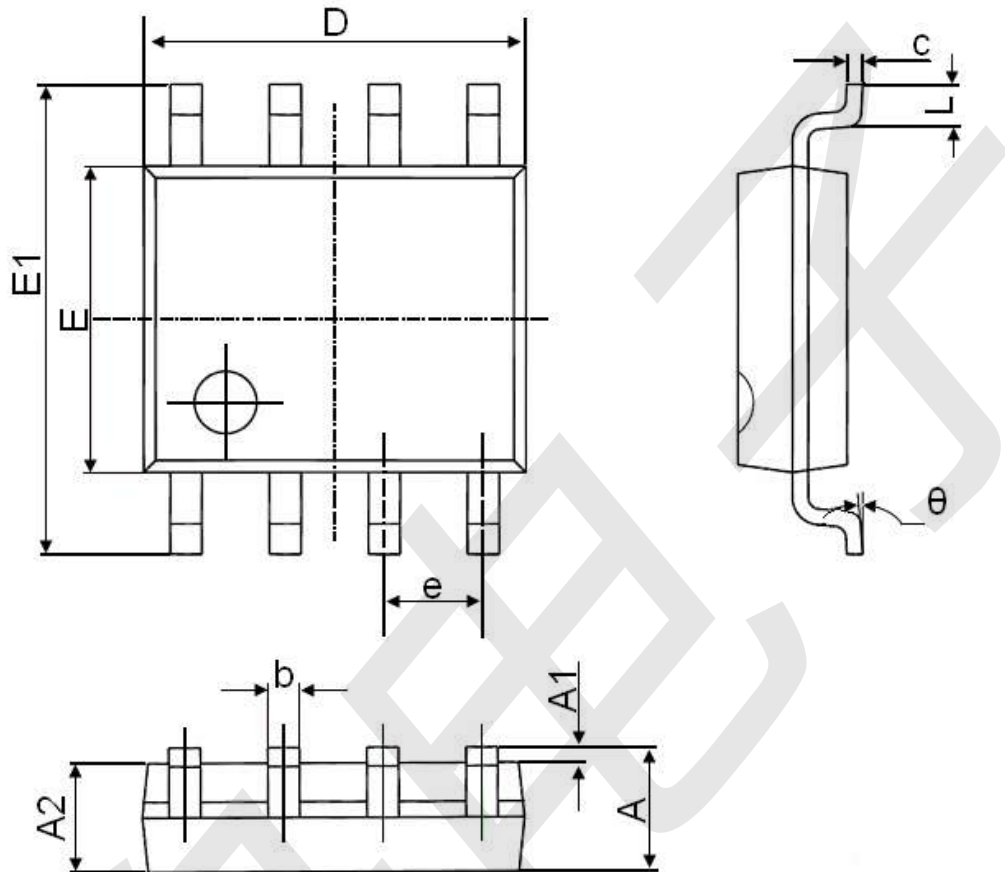
Symbol	Parameter	Limit	Min	Typ	Max	Unit
<b>STATIC</b>						
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250 μA	-1	-1.4	-3	V
I <sub>GSS</sub>	Gate Leakage Current	V <sub>DS</sub> =0V, V <sub>GS</sub> =±20V			±100	nA
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =-30V, V <sub>GS</sub> =0V			-1	μA
		V <sub>DS</sub> =-30V, V <sub>GS</sub> =0V T <sub>J</sub> =55			-25	
R <sub>DS(ON)</sub>	Drain-Source On-Resistance	V <sub>GS</sub> =-10V, I <sub>D</sub> = -5.3A		50	60	m
		V <sub>GS</sub> =-4.5V, I <sub>D</sub> = -4.2A		69	90	
V <sub>SD</sub>	Diode Forward Voltage	I <sub>S</sub> =-1.7A, V <sub>GS</sub> =0V		-0.8	-1.2	V
<b>DYNAMIC</b>						
R <sub>g</sub>	Gate resistance	V <sub>DS</sub> =0V, V <sub>GS</sub> =0V, f=1MHz		3.5		Ω
C <sub>iss</sub>	Input capacitance	V <sub>DS</sub> =-15V, V <sub>GS</sub> =0V, f=1.0MHz		450	490	pF
C <sub>oss</sub>	Output Capacitance			70		
C <sub>rss</sub>	Reverse Transfer Capacitance			20		
Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> =-15V, V <sub>GS</sub> =-10V, I <sub>D</sub> =-5.3A		14	17	nC
Q <sub>gs</sub>	Gate-Source Charge			4		
Q <sub>gd</sub>	Gate-Drain Charge			3		
t <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> =-15V, R <sub>L</sub> =15Ω I <sub>D</sub> =-1.0A, V <sub>GEN</sub> =-10V R <sub>G</sub> =6Ω		27	33	ns
t <sub>r</sub>	Turn-On Rise Time			11	15	
t <sub>d(off)</sub>	Turn-Off Delay Time			40	52	
t <sub>f</sub>	Turn-Off Fall Time			4	6	

### Typical Electrical and Thermal Characteristics





SOP-8 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270(BSC)		0.050(BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°